

IN THE SPECIFICATION

On page 10, please amend paragraph 0038 as follows:

Semiconductor component 100 additionally comprises a gate electrode 180 located over surface 111 of substrate 110. Gate electrode 180 is preferably located over at least a portion of channel region 120, non-electrically conductive region 130, drift region 141, electrically floating region 150, portion 170 of layer 112, and body region 171. Gate electrode 180 is also preferably located over at least a portion of source region 162, but is preferably not located over any portion of drain region 160. In an alternative embodiment, gate electrode 180 can be located over a portion of drain region 160. The location of gate electrode 180 over the edge or corner of electrically floating region [130] 150 and also over the portion of electrically floating region 150 at surface 111 of substrate 110 adjacent to the edge or corner of electrically floating region 130 both (a) reduces or at least eliminates the leakage current at the edge or corner of non-electrically conductive region 130 and (b) improves the drain-to-source sustaining voltage of the MOSFET in semiconductor component 100.